

## Amendment

### Amendment to the Claims

1. (withdrawn) A bipolar transistor (BJT) with reduced base-collector capacitance comprising  
an extrinsic base, and  
a lateral trench beneath the extrinsic base.
2. (withdrawn) A BJT of claim 1, wherein the trench is filled with air.
3. (withdrawn) A BJT of claim 1, wherein the trench is filled with an insulator.
4. (withdrawn) A BJT of claim 3, wherein the insulator is a high step coverable insulating material.
5. (withdrawn) A BJT of claim 4 wherein the insulator is PETEOS.
6. (withdrawn) A BJT of claim 1, wherein the trench has a  $\langle 110 \rangle$  orientation.
7. (withdrawn) A BJT of claim 6, wherein the trench is formed in a  $\langle 100 \rangle$  silicon wafer.
8. (canceled)
9. (canceled)
10. (currently amended) A method of forming a laterally extending trench in a semiconductor material underneath an extrinsic base of a BJT, comprising  
choosing a wafer with a  $\langle 100 \rangle$  crystal orientation,  
etching a vertically extending STI region next to the extrinsic base,  
and  
using an anisotropic etchant to etch the laterally extending trench  
to extend laterally from the STI,  
~~A method of claim 8, wherein the choosing of the crystal orientation is~~  
chosen so that the includes choosing a lateral trench extends direction that is in  
the  $\langle 110 \rangle$  direction.
11. (original) A method of claim 10, wherein the semiconductor material is silicon.

12. (original) A method of claim 11, wherein the etchant is a wet anisotropic silicon etchant.
13. (original) A method of claim 12, wherein the etchant includes KOH.
14. (original) A method of claim 13, wherein the etchant further includes alcohol and water.
15. (original) A method of claim 12, wherein the etchant includes TMAH.